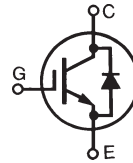


GenX3™ 1400V IGBTs w/ Diode

IXGH20N140C3H1 IXGT20N140C3H1

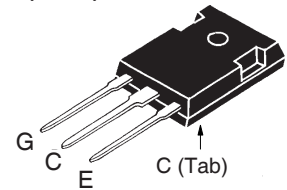
High-Speed PT IGBTs for 20 - 50 kHz Switching



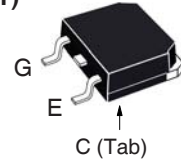
$$\begin{aligned} V_{CES} &= 1400V \\ I_{C100} &= 20A \\ V_{CE(sat)} &\leq 5.0V \\ t_{fi(typ)} &= 32ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1400	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1400	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	42	A
I_{C100}	$T_C = 100^\circ C$	20	A
I_{CM}	$T_C = 25^\circ C$, 1ms	108	A
I_A	$T_C = 25^\circ C$	20	A
E_{AS}	$T_C = 25^\circ C$	400	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 40$ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^\circ C$	250	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 (IXGH)



TO-268 (IXGT)



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Square RBSOA
- High Avalanche Capability
- Anti-Parallel Ultra Fast Diode
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$, Note 1			100 μA 2.0 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C100}$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	4.0 3.5	5.0	V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C100}, V_{CE} = 10\text{V}$, Note 1	10	17	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1790	pF
C_{oes}			145	pF
C_{res}			50	pF
Q_g	$I_C = I_{C100}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		88	nC
Q_{ge}			18	nC
Q_{gc}			30	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C100}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		19	ns
t_{ri}			12	ns
E_{on}			1.35	mJ
$t_{d(off)}$			110	ns
t_{fi}			32	ns
E_{off}			0.44	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C100}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		22	ns
t_{ri}			13	ns
E_{on}			2.33	mJ
$t_{d(off)}$			144	ns
t_{fi}			380	ns
E_{off}			1.64	mJ
R_{thJC}	TO-247		0.21	0.50°C/W
R_{thCK}				$^\circ\text{C/W}$

Reverse Diode (FRED)

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 20\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 125^\circ\text{C}$		2.8	3.0 V
I_{RM}	$I_F = 20\text{A}, V_{GE} = 0\text{V}$, $-di_F/dt = 750\text{A}/\mu\text{s}, V_R = 800\text{V}$		19	A
t_{rr}			70	ns
R_{thJC}				0.9°C/W

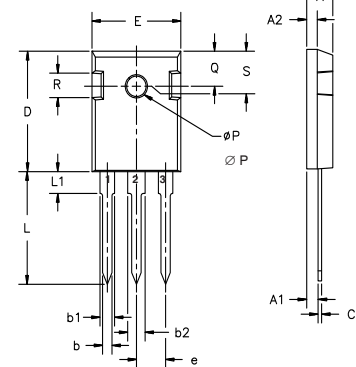
Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{Clamp})$, T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

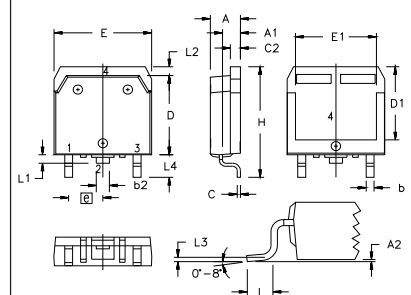
TO-247 Outline



Terminals: 1 - Gate
3 - Emitter
2 - Collector

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Terminals: 1 - Gate
3 - Emitter
2 & 4 - Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	